



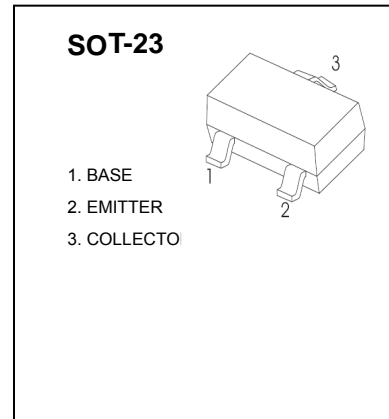
SOT-23 Plastic-Encapsulate Transistors

BC817-16 BC817-25

BC817-40 TRANSISTOR (NPN)

FEATURES

- For general AF applications
- High collector current
- High current gain
- Low collector-emitter saturation voltage
- Complementary types: BC807 (PNP)



MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	50	V
V_{CEO}	Collector-Emitter Voltage	45	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	0.5	A
P_C	Collector Power Dissipation	0.3	W
T_j	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55-150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CBO}	$I_C = 10\mu\text{A}, I_E = 0$	50			V
Collector-emitter breakdown voltage	V_{CEO}	$I_C = 10\text{mA}, I_B = 0$	45			V
Emitter-base breakdown voltage	V_{EBO}	$I_E = 1\mu\text{A}, I_C = 0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB} = 45\text{V}, I_E = 0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 4\text{V}, I_C = 0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = 1\text{V}, I_C = 100\text{mA}$	100		600	
	$h_{FE(2)}$	$V_{CE} = 1\text{V}, I_C = 500\text{mA}$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 500\text{mA}, I_B = 50\text{mA}$			0.7	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 500\text{mA}, I_B = 50\text{mA}$			1.2	V
Base-emitter voltage	V_{BE}	$V_{CE} = 1\text{V}, I_C = 500\text{mA}$			1.2	V
Collector capacitance	C_{ob}	$V_{CB} = 10\text{V}, f = 1\text{MHz}$		10		pF
Transition frequency	f_T	$V_{CE} = 5\text{V}, I_C = 10\text{mA}$ $f = 100\text{MHz}$	100			MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	BC817-16	BC817-25	BC817-40
Range	100-250	160-400	250-600
Marking	6A	6B	6C